

Bo E Sernelius

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176
papers

4,822
citations

32
h-index

67
g-index

191
ext. papers

5,204
ext. citations

2.6
avg, IF

5.66
L-index

#	Paper	IF	Citations
176	Band-gap tailoring of ZnO by means of heavy Al doping. <i>Physical Review B</i> , 1988 , 37, 10244-10248	3.3	732
175	Band-gap widening in heavily Sn-doped In ₂ O ₃ . <i>Physical Review B</i> , 1984 , 30, 3240-3249	3.3	530
174	Band-gap narrowing in heavily doped many-valley semiconductors. <i>Physical Review B</i> , 1981 , 24, 1971-1986	3.3	397
173	Defect related issues in the current roll-off in InGaN based light emitting diodes. <i>Applied Physics Letters</i> , 2007 , 91, 181103	3.4	248
172	Thermal effects on the casimir force in the 0.1- 5 μ m range. <i>Physical Review Letters</i> , 2000 , 84, 4757-60	3.3	243
171	Metal-insulator transition and superconductivity in boron-doped diamond. <i>Physical Review B</i> , 2007 , 75,	3.3	151
170	2001 ,		137
169	Electron-electron interactions and the bandwidth of metals. <i>Physical Review Letters</i> , 1989 , 62, 2718-2720	3.4	106
168	Retarded interactions in graphene systems. <i>Physical Review B</i> , 2012 , 85,	3.3	74
167	Fractional van der Waals interaction between thin metallic films. <i>Physical Review B</i> , 2000 , 61, 2204-2210	3.3	71
166	Band gap narrowing in n-type and p-type 3C-, 2H-, 4H-, 6H-SiC, and Si. <i>Journal of Applied Physics</i> , 1999 , 86, 4419-4427	2.5	69
165	Surface recombination in ZnO nanorods grown by chemical bath deposition. <i>Journal of Applied Physics</i> , 2008 , 104, 073526	2.5	67
164	Band-gap shifts in heavily p-type doped semiconductors of the zinc-blende and diamond type. <i>Physical Review B</i> , 1986 , 34, 5610-5620	3.3	67
163	Self-energy corrections in photoemission of Na. <i>Physical Review B</i> , 1987 , 36, 4499-4502	3.3	67
162	Casimir interactions in graphene systems. <i>Europhysics Letters</i> , 2011 , 95, 57003	1.6	65
161	Effects of spatial dispersion on electromagnetic surface modes and on modes associated with a gap between two half spaces. <i>Physical Review B</i> , 2005 , 71,	3.3	63
160	Reactively sputtered ZnO: Al films for energy-efficient windows. <i>Thin Solid Films</i> , 1988 , 164, 381-386	2.2	63

159	Band-gap shifts in heavily doped n-type GaAs. <i>Physical Review B</i> , 1986 , 33, 8582-8586	3-3	63
158	Two approaches for describing the Casimir interaction in graphene: Density-density correlation function versus polarization tensor. <i>Physical Review B</i> , 2014 , 89,	3-3	52
157	Entropy of the Casimir effect between real metal plates. <i>Physica A: Statistical Mechanics and Its Applications</i> , 2004 , 339, 53-59	3-3	52
156	Doping-induced effects on the band structure in n-type 3C ₂ H ₄ BiC, and Si. <i>Physical Review B</i> , 1999 , 60, 16479-16493	3-3	49
155	Optical properties of doped InGaN/GaN multiquantum-well structures. <i>Applied Physics Letters</i> , 1999 , 74, 3299-3301	3-4	48
154	Polarization propagator calculations of the polarizability tensor at imaginary frequencies and long-range interactions for the noble gases and n-alkanes. <i>Journal of Chemical Physics</i> , 2003 , 118, 9167-9174	3-9	46
153	Interaction energy for a pair of quantum wells. <i>Physical Review B</i> , 1998 , 57, 6592-6601	3-3	45
152	Optical absorption of Li-intercalated polycrystalline tungsten oxide films: comparison to large polaron theory. <i>Solid State Ionics</i> , 2003 , 165, 35-41	3-3	43
151	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. <i>Applied Physics Letters</i> , 2009 , 94, 022109	3-4	38
150	Self-energy shifts in heavily doped, polar semiconductors. <i>Physical Review B</i> , 1987 , 36, 4878-4887	3-3	38
149	Electron states in heavily doped semiconductors. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1981 , 43, 115-148		37
148	Electric dipole polarizabilities and C ₆ dipole-dipole dispersion coefficients for sodium clusters and C ₆₀ . <i>Journal of Chemical Physics</i> , 2006 , 125, 124306	3-9	34
147	Dynamical conductivity in the infrared from impurity scattering in a polar semiconductor. <i>Physical Review B</i> , 1987 , 36, 1080-1089	3-3	34
146	Effects of quantum confinement in a special GaAs field effect transistor: on the DC conductance in the regime of metallic transport. <i>Journal of Physics C: Solid State Physics</i> , 1985 , 18, 225-240		33
145	Electron mobility enhancement in Si using doubly doped layers. <i>Applied Physics Letters</i> , 1994 , 64, 1842-1844	3-4	32
144	Intervalley mixing versus disorder in heavily doped n-type silicon. <i>Physical Review B</i> , 1984 , 29, 5575-5580	3-3	32
143	Complex polarization propagator method for calculation of dispersion coefficients of extended pi-conjugated systems: the C ₆ coefficients of polyacenes and C ₆₀ . <i>Journal of Chemical Physics</i> , 2005 , 123, 124312	3-9	31
142	Generalized Drude approach to the conductivity relaxation time due to electron-hole collisions in optically excited semiconductors. <i>Physical Review B</i> , 1989 , 40, 12438-12440	3-3	29

141	Retardation turns the van der Waals attraction into a Casimir repulsion as close as 3 nm. <i>Physical Review A</i> , 2012 , 85,	2.6	26
140	Finite-temperature Casimir force between metal plates: full inclusion of spatial dispersion resolves a long-standing controversy. <i>Journal of Physics A</i> , 2006 , 39, 6741-6752		24
139	Electrical resistivity and metal-nonmetal transition in n-type doped 4H β SiC. <i>Physical Review B</i> , 2006 , 74,	3.3	23
138	van der Waals energy of an atom in the proximity of thin metal films. <i>Physical Review A</i> , 2000 , 61,	2.6	22
137	Temperature-dependent resistivity of heavily doped silicon and germanium. <i>Physical Review B</i> , 1990 , 41, 3060-3068	3.3	22
136	Repulsive van der Waals forces due to hydrogen exposure on bilayer graphene. <i>Physical Review A</i> , 2012 , 85,	2.6	21
135	Comment on "Casimir force at both nonzero temperature and finite conductivity". <i>Physical Review Letters</i> , 2001 , 87, 259101	7.4	21
134	C6 dipole-dipole dispersion coefficients for the n-alkanes: Test of an additivity procedure. <i>Physical Review A</i> , 2004 , 69,	2.6	20
133	Comment on "Calculation of the Casimir force between imperfectly conducting plates" <i>Physical Review A</i> , 2000 , 61,	2.6	20
132	Electron-hole liquid in layered InSe: Comparison of two- and three-dimensional excitonic states. <i>Physical Review B</i> , 1986 , 33, 8568-8581	3.3	19
131	Very heavily doped semiconductors as a "nearly-free-electron-gas" system. <i>Solid-State Electronics</i> , 1985 , 28, 11-15	1.7	19
130	Bandgap widening in heavily doped oxide semiconductors used as transparent heat-reflectors. <i>Solar Energy Materials and Solar Cells</i> , 1985 , 12, 479-490		19
129	Effective electron and hole masses in intrinsic and heavily n-type doped GaN and AlN. <i>Journal of Physics Condensed Matter</i> , 2001 , 13, 8915-8922	1.8	18
128	Transport properties of silicon implanted with bismuth. <i>Physical Review B</i> , 1997 , 55, 9584-9589	3.3	17
127	Casimir force and complications in the van Kampen theory for dissipative systems. <i>Physical Review B</i> , 2006 , 74,	3.3	17
126	Sernelius Replies. <i>Physical Review Letters</i> , 2001 , 87,	7.4	17
125	Plasma-induced band edge shifts in 3C-, 2H-, 4H-, 6H β SiC and Si. <i>Solid-State Electronics</i> , 2000 , 44, 471-476	1.7	17
124	Intraband relaxation time in highly excited semiconductors. <i>Physical Review B</i> , 1991 , 43, 7136-7144	3.3	17

123	Impurity resistivity of the double-donor system Si:P,Bi. <i>Physical Review B</i> , 1999 , 60, 15824-15828	3.3	16
122	Casimir effects in systems containing 2D layers such as graphene and 2D electron gases. <i>Journal of Physics Condensed Matter</i> , 2015 , 27, 214017	1.8	15
121	Optical and reduced band gap in n- and p-type GaN and AlN. <i>Journal of Applied Physics</i> , 2002 , 92, 3207-3216	3.3	15
120	Theoretical optical properties of polar semiconductors used as optical coatings for energy-efficient windows. <i>Thin Solid Films</i> , 1989 , 177, 69-75	2.2	15
119	Casimir force between atomically thin gold films. <i>European Physical Journal B</i> , 2013 , 86, 1	1.2	14
118	Exciton properties in p-type GaAs/Al _x Ga _{1-x} As quantum wells in the high doping regime. <i>Physical Review B</i> , 1996 , 54, 16989-16993	3.3	14
117	Core-level spectra from graphene. <i>Physical Review B</i> , 2015 , 91,	3.3	13
116	Casimir attractive-repulsive transition in MEMS. <i>European Physical Journal B</i> , 2012 , 85, 1	1.2	12
115	Temperature effects on the Casimir attraction between a pair of quantum wells. <i>Microelectronic Engineering</i> , 2000 , 51-52, 287-297	2.5	12
114	Influence of potential fluctuations on electrical transport and optical properties in modulation-doped GaN/Al _{0.28} Ga _{0.72} N heterostructures. <i>Physical Review B</i> , 1998 , 58, 1442-1450	3.3	12
113	Tunneling current spectroscopy of electron subbands in n-type doped silicon structures grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1990 , 67, 1962-1968	2.5	12
112	Polaron in n dimensions. <i>Physical Review B</i> , 1987 , 36, 9059-9067	3.3	12
111	Ultrafast dynamic conductivity and scattering rate saturation of photoexcited charge carriers in silicon investigated with a midinfrared continuum probe. <i>Physical Review B</i> , 2015 , 91,	3.3	11
110	Electromagnetic normal modes and Casimir effects in layered structures. <i>Physical Review B</i> , 2014 , 90,	3.3	11
109	Beyond the simple proximity force approximation: Geometrical effects on the nonretarded Casimir interaction. <i>Physical Review A</i> , 2008 , 78,	2.6	11
108	Photoluminescence study of Si-doped GaN/Al _{0.07} Ga _{0.93} N multiple quantum wells with different dopant position. <i>Applied Physics Letters</i> , 2004 , 84, 5071-5073	3.4	11
107	Electron mean free path in Be metal. <i>Physical Review B</i> , 1994 , 50, 16817-16823	3.3	11
106	Electrical characterization and subband structures in antimony doped molecular beam epitaxy-silicon layers. <i>Thin Solid Films</i> , 1989 , 183, 331-338	2.2	11

105	Theoretical high-stress optical birefringence and piezoresistance in heavily doped germanium. Arguments against band tailing. <i>Physical Review B</i> , 1983 , 27, 6234-6245	3.3	11
104	Graphene as a Strictly 2D Sheet or as a Film of Small but Finite Thickness. <i>Graphene</i> , 2012 , 01, 21-25	1.5	11
103	Casimir experiments showing saturation effects. <i>Physical Review A</i> , 2009 , 80,	2.6	10
102	Ultrathin metallic coatings can induce quantum levitation between nanosurfaces. <i>Applied Physics Letters</i> , 2012 , 100, 253104	3.4	10
101	Electrical resistivity of acceptor carbon in GaAs. <i>Journal of Applied Physics</i> , 2004 , 95, 2532-2535	2.5	10
100	Electrical resistivity and band-gap shift of Si-doped GaN and metal-nonmetal transition in cubic GaN, InN and AlN systems. <i>Journal of Crystal Growth</i> , 2001 , 231, 420-427	1.6	10
99	Retardation-enhanced van der Waals force between thin metal films. <i>Physical Review B</i> , 2000 , 62, 7523-7526	3.3	10
98	Many-body effects in highly acceptor-doped GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 1998 , 58, 4624-4628	3.3	10
97	Metal-nonmetal transition and resistivity of silicon implanted with bismuth. <i>Journal of Materials Research</i> , 1997 , 12, 641-645	2.5	9
96	First principle calculations of dipole-dipole dispersion coefficients for the ground and first excited states of some azabenzenes. <i>Journal of Computational Methods in Sciences and Engineering</i> , 2004 , 4, 321-332	0.3	9
95	Possible induced enhancement of dispersion forces by cellular phones. <i>Physical Chemistry Chemical Physics</i> , 2004 , 6, 1363-1368	3.6	9
94	Many-body effects in highly p-type modulation-doped GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 2000 , 61, 2794-2798	3.3	9
93	Thermally activated intersubband and hopping transport in center-doped p-type GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 1996 , 53, 1357-1361	3.3	9
92	Intermolecular Casimir-Polder forces in water and near surfaces. <i>Physical Review E</i> , 2014 , 90, 032122	2.4	8
91	Attractive double-layer forces between neutral hydrophobic and neutral hydrophilic surfaces. <i>Physical Review E</i> , 2011 , 84, 061903	2.4	8
90	Forces between air-bubbles in electrolyte solution. <i>Chemical Physics Letters</i> , 2008 , 458, 299-302	2.5	8
89	Influence of Si doping on optical properties of wurtzite GaN. <i>Journal of Physics Condensed Matter</i> , 2001 , 13, 8891-8899	1.8	8
88	Acoustic-phonon anomaly in MgB ₂ . <i>Physical Review B</i> , 2002 , 66,	3.3	8

87	Band-gap shift of the heavily doped single- and double-donor systems Si:Bi and Si:P,Bi. <i>Physical Review B</i> , 2000 , 62, 12882-12887	3.3	8
86	Optical free-carrier absorption of an electron-hole plasma in silicon. <i>Physical Review B</i> , 1989 , 39, 10825-10830	3.3	8
85	Origin of negative magnetoresistance in heavily doped n-type silicon and germanium. <i>Physical Review B</i> , 1979 , 19, 6390-6396	3.3	8
84	Phonon replicas of charged and neutral exciton complexes in single quantum dots. <i>Physical Review B</i> , 2010 , 82,	3.3	7
83	Wetting problems for coatings on windshields. <i>Applied Surface Science</i> , 1999 , 142, 375-380	6.7	7
82	Casimir forces in a plasma: possible connections to Yukawa potentials. <i>European Physical Journal D</i> , 2014 , 68, 1	1.3	6
81	Electrical resistivity of bismuth implanted into silicon. <i>Journal of Applied Physics</i> , 1996 , 79, 3453-3455	2.5	6
80	Polarized hot-electron photoluminescence in highly doped GaAs. <i>Physical Review B</i> , 1986 , 34, 8696-8702	3.3	6
79	Sign of the Casimir-Polder interaction between atoms and oil-water interfaces: Subtle dependence on dielectric properties. <i>Physical Review A</i> , 2012 , 85,	2.6	5
78	CASIMIR EFFECTS IN GRAPHENE SYSTEMS: UNEXPECTED POWER LAWS. <i>International Journal of Modern Physics Conference Series</i> , 2012 , 14, 531-540	0.7	5
77	Test of the Proximity Force Approximation. <i>Journal of Physics: Conference Series</i> , 2009 , 161, 012016	0.3	5
76	Electrical resistivity, MNM transition and band-gap narrowing of cubic GaN:Si. <i>Microelectronics Journal</i> , 2002 , 33, 365-369	1.8	5
75	The zero-temperature d.c. conductivity versus density and the metal-insulator transition in some heavily doped semiconductor systems. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1985 , 52, 459-469		5
74	Fundamentals of van der Waals and Casimir Interactions. <i>Springer Series on Atomic, Optical, and Plasma Physics</i> , 2018 ,	0.4	5
73	Magnetoresistance of doped silicon. <i>Physical Review B</i> , 2015 , 91,	3.3	4
72	Enlarged molecules from excited atoms in nanochannels. <i>Physical Review A</i> , 2012 , 86,	2.6	4
71	Strong enhancement of dispersion forces from microwave radiation. <i>Europhysics Letters</i> , 2002 , 60, 643-648	4.8	4
70	Carrier and exciton dynamics in In _{0.15} Ga _{0.85} N GaN multiple quantum well structures 1999 ,		4

69	Free-polaron absorption. <i>Physical Review B</i> , 1993 , 48, 7043-7049	3.3	4
68	Theories of impurity resistivity. <i>Journal of Physics Condensed Matter</i> , 1991 , 3, 1493-1504	1.8	4
67	Casimir-Lifshitz interaction between ZnO and SiO ₂ nanorods in bromobenzene turns repulsive at intermediate separations due to retardation effects. <i>Physical Review A</i> , 2012 , 85,	2.6	3
66	Numerical study of the effect of structure and geometry on van der Waals forces. <i>Journal of Physics A: Mathematical and Theoretical</i> , 2008 , 41, 164008	2	3
65	Effects of electron-electron scattering on impurity resistivity. <i>Journal of Physics Condensed Matter</i> , 1991 , 3, 8425-8432	1.8	3
64	Temperature dependence of the transmittance, reflectance and absorption of optical films. <i>Thin Solid Films</i> , 1992 , 208, 96-99	2.2	3
63	Free-carrier absorption from Fibonacci sequences of delta -doped layers in silicon. <i>Physical Review B</i> , 1989 , 40, 6218-6221	3.3	3
62	Theoretical predictions for the surface states on Ge(111)2 x 1: The degree of antibonding surface-state filling and relative shifts of the two surface-state bands as functions of doping level. <i>Physical Review B</i> , 1986 , 33, 2949-2952	3.3	3
61	Bandgap Widening In Heavily Doped Oxide Semiconductors Used As Transparent Heat-Reflectors 1984 , 0502, 2		3
60	Nonperturbative theory for the dispersion self-energy of atoms. <i>Physical Review A</i> , 2014 , 90,	2.6	2
59	Resonance interaction induced by metal surfaces catalyzes atom-pair breakage. <i>Physical Review A</i> , 2013 , 87,	2.6	2
58	Lithium atom storage in nanoporous cellulose via surface-induced Li 2 breakage. <i>Europhysics Letters</i> , 2013 , 104, 63003	1.6	2
57	GRAVITATION AS A CASIMIR EFFECT. <i>International Journal of Modern Physics A</i> , 2009 , 24, 1804-1812	1.2	2
56	Saturation effects in experiments on the thermal Casimir effect. <i>Europhysics Letters</i> , 2009 , 87, 14004	1.6	2
55	Current drag in a single quantum well. <i>Journal of Physics Condensed Matter</i> , 1996 , 8, 3705-3714	1.8	2
54	Plasmon shake-up effects in quantum-well exciton spectra. <i>Journal of Physics Condensed Matter</i> , 1996 , 8, 9071-9081	1.8	2
53	Evidence of Potential Fluctuations in Modulation Doped GaN/AlGa _N Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 482, 623		2
52	The energy spectrum of electromagnetic normal modes in dissipative media: modes between two metal half spaces. <i>Journal of Physics A: Mathematical and Theoretical</i> , 2008 , 41, 164016	2	2

51	Reply to Comment on Effects of spatial dispersion on electromagnetic surface modes and on modes associated with a gap between two half spaces. <i>Physical Review B</i> , 2007 , 75,	3.3	2
50	Comment on Possible induced enhancement of dispersion forces by cellular phones by B. E. Sernelius, Phys. Chem. Chem. Phys., 2004, 6, 1363. <i>Physical Chemistry Chemical Physics</i> , 2004 , 6, 3915-3915	3.6	2
49	Effects of van der Waals Interaction on Current Drag between Quantum Wells. <i>Physica Scripta</i> , 1999 , T79, 89	2.6	2
48	Spectroscopy studies of highly acceptor doped GaAs/AlGaAs quantum wells. <i>Superlattices and Microstructures</i> , 1995 , 18, 153-155	2.8	2
47	Dimensional crossover for a quasi-one-dimensional polaron. <i>Physical Review B</i> , 1988 , 37, 7079-7082	3.3	2
46	Elementary excitations and quasi-two-dimensional behavior in a GaAs field-effect transistor. <i>Physical Review B</i> , 1984 , 30, 1016-1018	3.3	2
45	Electron states in heavily doped semiconductors. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1980 , 42, 751-754		2
44	Non-perturbative theory of dispersion interactions. <i>Physica Scripta</i> , 2015 , 90, 035405	2.6	1
43	Finite-size-dependent dispersion potentials between atoms and ions dissolved in water. <i>Europhysics Letters</i> , 2014 , 106, 53002	1.6	1
42	Core-level spectra from bilayer graphene. <i>FlatChem</i> , 2017 , 1, 6-10	5.1	1
41	Atmospheric water droplets can catalyse atom pair break-up via surface-induced resonance repulsion. <i>Europhysics Letters</i> , 2013 , 101, 43002	1.6	1
40	THE THERMAL CASIMIR EFFECT: SATURATION. <i>International Journal of Modern Physics A</i> , 2010 , 25, 2319-2327		1
39	Electric dipole polarizabilities and C6 dipole-dipole dispersion coefficients for alkali metal clusters and C60. <i>Journal of Computational Methods in Sciences and Engineering</i> , 2008 , 7, 475-488	0.3	1
38	Si Layers embedded in GaAs. <i>Applied Physics Letters</i> , 1998 , 73, 3709-3711	3.4	1
37	Mechanism for Radiative Recombination in In _{0.15} Ga _{0.85} N/GaN Multiple Quantum Well Structures. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		1
36	Optical and transport studies of highly acceptor doped GaAs/AlGaAs quantum wells. <i>Surface Science</i> , 1996 , 361-362, 420-423	1.8	1
35	Optical studies of acceptor centre doped quantum wells. <i>Solid-State Electronics</i> , 1996 , 40, 89-92	1.7	1
34	Bandgap Widening in Heavily Sn-Doped In ₂ O ₃ 1985 , 1051-1054		1

33	Heavily n-doped Ge: Low-temperature magnetoresistance properties on the metallic side of the metal-nonmetal transition. <i>Journal of Applied Physics</i> , 2020 , 127, 045705	2.5	0
32	Relativistic Doppler reflection as a probe for the initial relaxation of a non-equilibrium electron-hole plasma in silicon. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012016	0.3	0
31	Mechanism for Radiative Recombination in In _{0.15} Ga _{0.85} N/GaN Multiple Quantum Well Structures. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 87-92		0
30	Impurity resistivity in doubly doped systems. <i>Physica Scripta</i> , 1997 , T69, 286-289	2.6	
29	Properties of Si layers embedded in GaAs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998 , 2, 247-251	3	
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19	Modes at non-planar interfaces 2005 , 257-284		
18	Modes at flat interfaces 2005 , 99-165		
17	Reply to the Comment on Possible induced enhancement of dispersion forces by cellular phones[] by R. K. Adair, Phys. Chem. Chem. Phys., 2004, 6, DOI: 10.1039/b405698a. <i>Physical Chemistry Chemical Physics</i> , 2004 , 6, 3916-3916	3.6	
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- 15 Excitation-induced optical switching in transparent coatings. *Thin Solid Films*, **1996**, 278, 104-107 2.2
- 14 Theories of impurity resistivity in two dimensions. *Journal of Physics Condensed Matter*, **1993**, 5, 335-344 1.8
- 13 CAN THE RADIATION FROM CELLULAR PHONES HAVE IMPORTANT EFFECTS ON THE FORCES BETWEEN BIOLOGICAL TISSUE-COMPONENTS? **2006**, 355-366
- 12 Van der Waals Interaction in Spherical Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 209-232 0.4
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